AMENDMENT TRANSMITTAL LETTER (Large Entity) Applicant(s): Tsukasa YAJIMA							Docket No. PNET.009D	
Serial No. 09/768,271 Ja		_	Filing Date January 25, 2001		Examiner A. Mai		Group Art Unit 2814	
Invention; PSEVICONDUCTOR DEVICE HAVING PROTECTIVE LAYER ON FIELD OXIDE								
TO THE ASSISTANT COMMISSIONER FOR PATENTS: Transmitted herewith is an amendment in the above-identified application. The fee has been calculated and is transmitted as shown below.								
CLAIMS AS AMENDED								
	CLAIMS REMAINING AFTER AMENDMENT		HIGHEST #	NUMBEF	R EXTRA PRESENT	RATE	ADDITIONAL FEE	
TOTAL CLAIMS		9 -		=	0 >	ς \$18	3.00 \$0.00	
INDEP. CLAIMS	NDEP. CLAIMS 2 -			=	0	\$8 4	\$0.00	
Multiple Dependent Claims (check if applicable) \$0.00								
TOTAL ADDITIONAL FEE FOR THIS AMENDMENT \$0.00								
No additional fee is required for amendment. ☐ Please charge Deposit Account No. in the amount of A duplicate copy of this sheet is enclosed. ☐ A check in the amount of to cover the filing fee is enclosed. ☐ The Commissioner is hereby authorized to charge payment of the following fees associated with this communication or credit any overpayment to Deposit Account No. 50-0238 A duplicate copy of this sheet is enclosed. ☐ Any additional filing fees required under 37 C.F.R. 1.16. ☐ Any patent application processing fees under 37 CFR 1.17. ☐ Dated: December 31, 2001								
REG. NO. 33,58 VOLENTINE F 12200 SUNRISH RESTON, VA 2 TEL. NO.: (703)	RANCO E VALL 20191	EY DRIVE, SUI	TE 150		on first class ma Assistant Co 20231.	il under 37 mmissione	with the U.S. Postal Service a C.F.R. 1.8 and is addressed to the for Patents, Washington, D.C. rson Mailing Correspondence	



PNET.009P

THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re PATENT APPLICATION of

Tsukasa Yajima

Group Art Unit: 2814

Serial No.: 09/768,274

Examiner: A. Mai

Filed: January 25, 2001

For: SEMICONDUCTOR DEVICE HAVING PROTECTIVE LAYER ON FIELD OXIDE

(As Amended)

AMENDMENT

Honorable Assistant Commissioner for Patents Washington, D.C. 20231

Date: December 31, 2001

Sir:

In response to the Office Action dated October 12, 2001, the following amendments and remarks are respectfully submitted in connection with the above-identified application.

In the Claims:

Please cancel claims 4, 5 and 10 without prejudice or disclaimer of the subject matter contained therein.

The following replacement claims are respectfully submitted:

6. (Amended) A semiconductor device comprising:

first and second gates formed on active regions of a substrate;

a field oxide formed on the substrate between said first and second gates;